

# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Character	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 4) V <sub>GS</sub> = 4.0V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	0.27 0.21	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.0V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	0.31 0.25	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.0V	t ≤ 10s	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	0.38 0.3	А
Continuous Drain Current (Note 4) V <sub>GS</sub> = 2.5V	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	I <sub>D</sub>	0.21 0.15	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 2.5V	t ≤ 10s	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	I <sub>D</sub>	0.29 0.22	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	1.2	Α

## **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P <sub>D</sub>	0.28	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 4)	$R_{\theta JA}$	474	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	0.36	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 5)	R <sub>θJA</sub>	361	°C/W
Power Dissipation (Note 5) t ≤ 10s	P <sub>D</sub>	0.52	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 5) t ≤ 10s	$R_{\theta JA}$	252	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C

## Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise stated

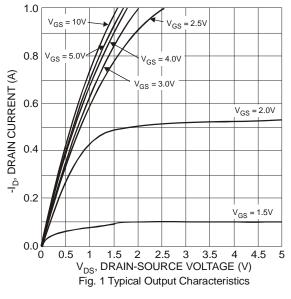
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	0.1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±1.0	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)		-					
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	-	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	1.3	2	Ω	$V_{GS} = 4V, I_{D} = 10mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	1.6	3.2		$V_{GS} = 2.5V, I_D = 1mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	93	-	mS	$V_{DS} = 3V$ , $I_D = 10mA$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	-	36.3	-		)/ 5)/ )/ O)/	
Output Capacitance	Coss	-	7.6	-	pF	$V_{DS} = 5V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	4.7	-			
Gate Resistance	Rg	-	128	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	-	0.5	-			
Gate-Source Charge	Q <sub>qs</sub>	-	0.1	-	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 10\text{mA}$	
Gate-Drain Charge	Q <sub>qd</sub>	-	0.1	-			
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.5	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	2.24	-	ns	$V_{GS} = 4.5V, V_{DS} = 15V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	19.2	-	ns	$R_G = 2\Omega$ ,	
Turn-Off Fall Time	t <sub>f</sub>	-	28.2	-	ns	$I_D = 180 \text{mA}$	

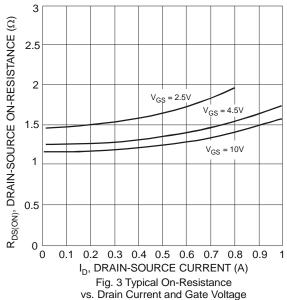
Notes:

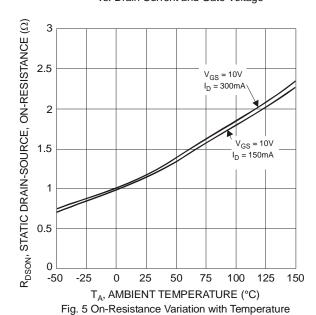
- 4. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 5. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
- Short duration pulse width limited by junction temperature.
  Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.



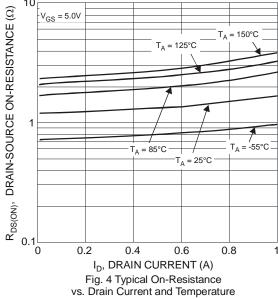








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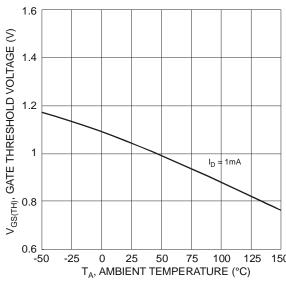
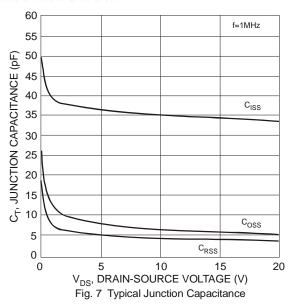
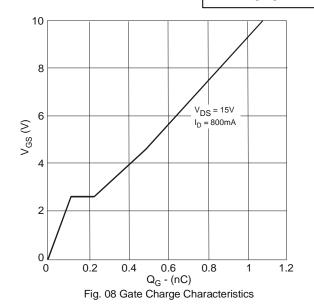


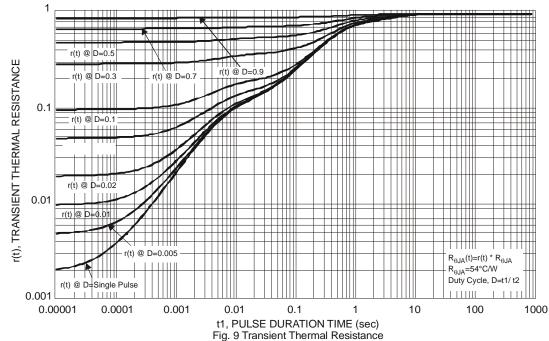
Fig. 6 Gate Threshold Variation vs. Ambient Temperature



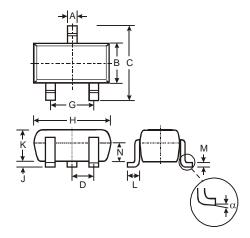
## DMN313DLT







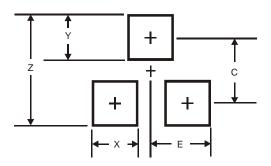
## **Package Outline Dimensions**



	SOT-523					
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
С	1.45	1.75	1.60			
D			0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
J	0.00	0.10	0.05			
K	0.60	0.80	0.75			
L	0.10	0.30	0.22			
M	0.10	0.20	0.12			
N	0.45	0.65	0.50			
α	0°	8°	_			
All Dimensions in mm						



### **Suggested Pad Layout**



Dimensions	Value (in mm)			
Z	1.8			
Х	0.4			
Υ	0.51			
С	1.3			
E	0.7			

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